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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RS08
Core Size	8-Bit
Speed	20MHz
Connectivity	I ² C, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	6
Program Memory Size	2KB (2K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	126 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	8-SOIC (0.154", 3.90mm Width)
Supplier Device Package	8-SOIC
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9rs08kb2cscr

Part Number	Package Description	Original (gold wire) package document number	Current (copper wire) package document number
MC68HC908JW32	48 QFN	98ARH99048A	98ASA00466D
MC9S08AC16			
MC9S908AC60			
MC9S08AC128			
MC9S08AW60			
MC9S08GB60A			
MC9S08GT16A			
MC9S08JM16			
MC9S08JM60			
MC9S08LL16			
MC9S08QE128			
MC9S08QE32			
MC9S08RG60			
MCF51CN128			
MC9RS08LA8	48 QFN	98ARL10606D	98ASA00466D
MC9S08GT16A	32 QFN	98ARH99035A	98ASA00473D
MC9S908QE32	32 QFN	98ARE10566D	98ASA00473D
MC9S908QE8	32 QFN	98ASA00071D	98ASA00736D
MC9S08JS16	24 QFN	98ARL10608D	98ASA00734D
MC9S08QB8			
MC9S08QG8	24 QFN	98ARL10605D	98ASA00474D
MC9S08SH8	24 QFN	98ARE10714D	98ASA00474D
MC9RS08KB12	24 QFN	98ASA00087D	98ASA00602D
MC9S08QG8	16 QFN	98ARE10614D	98ASA00671D
MC9RS08KB12	8 DFN	98ARL10557D	98ASA00672D
MC9S08QG8			
MC9RS08KA2	6 DFN	98ARL10602D	98ASA00735D



MC9RS08KB12 Series

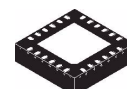
Covers: MC9RS08KB12
MC9RS08KB8
MC9RS08KB4
MC9RS08KB2

- 8-Bit RS08 Central Processor Unit (CPU)
 - Up to 20 MHz CPU at 1.8 V to 5.5 V across temperature range of –40 °C to 85 °C
 - Subset of HC08 instruction set with added BGND instruction
 - Single Global interrupt vector
- On-Chip Memory
 - Up to 12 KB flash read/program/erase over full operating voltage and temperature, 12 KB/8 KB/4 KB/2 KB flash are optional
 - Up to 254-byte random-access memory (RAM), 254-byte/126-byte RAM are optional
 - Security circuitry to prevent unauthorized access to flash contents
- Power-Saving Modes
 - Wait mode — CPU shuts down; system clocks continue to run; full voltage regulation
 - Stop mode — CPU shuts down; system clocks are stopped; voltage regulator in standby
 - Wakeup from power-saving modes using RTI, KBI, ADC, ACMP, SCI and LVD
- Clock Source Options
 - Oscillator (XOSC) — Loop-control Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 39.0625 kHz or 1 MHz to 16 MHz
 - Internal Clock Source (ICS) — Internal clock source module containing a frequency-locked-loop (FLL) controlled by internal or external reference; precision trimming of internal reference allows 0.2% resolution and 2% deviation over temperature and voltage; supporting bus frequencies up to 10 MHz
- System Protection
 - Watchdog computer operating properly (COP) reset with option to run from dedicated 1 kHz internal low power oscillator
 - Low-voltage detection with reset or interrupt
 - Illegal opcode detection with reset
 - Illegal address detection with reset
 - Flash-block protection

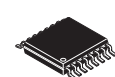
MC9RS08KB12



20-Pin SOIC
Case 751D



24-Pin QFN
Case 1982-01



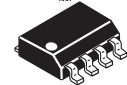
16-Pin TSSOP
Case 948F



16-Pin SOIC N/B
Case 751B



8-Pin DFN
Case 1452-02



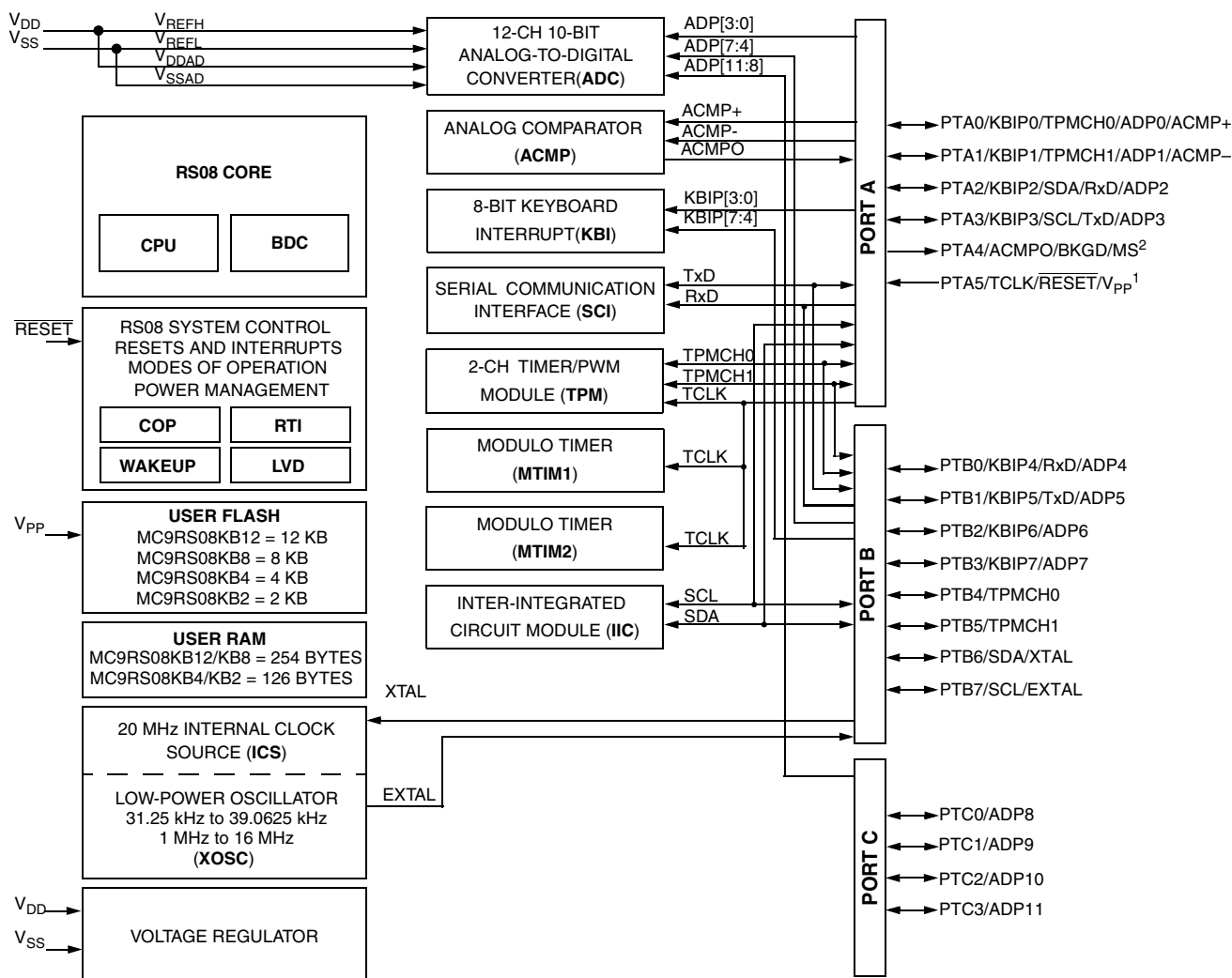
8-Pin SOIC
Case 751

- Development Support
 - Single-wire background debug interface
 - Breakpoint capability to allow single breakpoint setting during in-circuit debugging
- Peripherals
 - **ADC** — 12-channel, 10-bit resolution; 2.5 μ s conversion time; automatic compare function; 1.7 mV/°C temperature sensor; internal bandgap reference channel; operation in stop; hardware trigger
 - **ACMP** — Analog comparator; full rail-to-rail supply operation; option to compare to fixed internal bandgap reference voltage; can operate in stop mode
 - **TPM** — One 2-channel timer/pulse-width modulator module; selectable input capture, output compare, or buffered edge- or center-aligned PWM on each channel
 - **IIC** — Inter-integrated circuit bus module capable of operation up to 100 kbps with maximum bus loading; capable of higher baud rates with reduced loading
 - **SCI** — One serial communications interface module with optional 13-bit break; LIN extensions
 - **MTIM** — Two 8-bit modulo timers; optional clock sources
 - **RTI** — One real-time clock with optional clock sources
 - **KBI** — Keyboard interrupts; up to 8 ports
- Input/Output
 - 18 GPIOs in 24- and 20-pin packages; 14 GPIOs in 16-pin package; 6 GPIOs in 8-pin package; including one output-only pin and one input-only pin
 - Hysteresis and configurable pullup device on all input pins; configurable slew rate and drive strength on all output pins
- Package Options
 - MC9RS08KB12/MC9RS08KB8/MC9RS08KB4
 - 24-pin QFN, 20-pin SOIC, 16-pin SOIC NB or TSSOP
 - MC9RS08KB2
 - 8-pin SOIC or DFN

This document contains information on a product under development. Freescale reserves the right to change or discontinue this product without notice.

1 MCU Block Diagram

The block diagram, [Figure 1](#), shows the structure of the MC9RS08KB12 MCU.



NOTES:

1. PTA5/TCLK/RESET/V_{PP} is an input-only pin when used as port pin
2. PTA4/ACMPO/BKGD/MS is an output-only pin when used as port pin

Figure 1. MC9RS08KB12 Series Block Diagram

2 Pin Assignments

This section shows the pin assignments in the packages available for the MC9RS08KB12 series.

Table 1. Pin Availability by Package Pin-Count

Pin Number				<-- Lowest Priority --> Highest				
24	20	16	8	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
1	3	3	3					V _{DD}
2	—	—	—	NC				
3	4	4	4					V _{SS}
4	5	5	—	PTB7	SCL ¹			EXTAL
5	6	6	—	PTB6	SDA ¹			XTAL
6	7	7	—	PTB5	TPMCH1 ²			
7	8	8	—	PTB4	TPMCH0 ²			
8	9	—	—	PTC3			ADP11	
9	10	—	—	PTC2			ADP10	
10	11	—	—	PTC1			ADP9	
11	12	—	—	PTC0			ADP8	
12	13	9	—	PTB3	KBIP7		ADP7	
13	14	10	—	PTB2	KBIP6		ADP6	
14	15	11	—	PTB1	KBIP5	TxD ³	ADP5	
15	16	12	—	PTB0	KBIP4	RxD ³	ADP4	
16	17	13	5	PTA3	KBIP3	SCL ¹	TxD ³	ADP3
17	18	14	6	PTA2	KBIP2	SDA ¹	RxD ³	ADP2
18	19	15	7	PTA1	KBIP1	TPMCH1 ²	ADP1	ACMP–
19	20	16	8	PTA0	KBIP0	TPMCH0 ²	ADP0	ACMP+
20	—	—	—	NC				
21	—	—	—	NC				
22	—	—	—	NC				
23	1	1	1	PTA5		TCLK	RESET	V _{PP}
24	2	2	2	PTA4	ACMPO	BKGD	MS	

¹ IIC pins can be remapped to PTB6 and PTB7, default reset location is PTA2 and PTA3. It can be configured only once.

² TPM pins can be remapped to PTB4 and PTB5, default reset location is PTA0 and PTA1.

³ SCI pins can be remapped to PTA2 and PTA3, default reset location is PTB0 and PTB1. It can be configured only once.

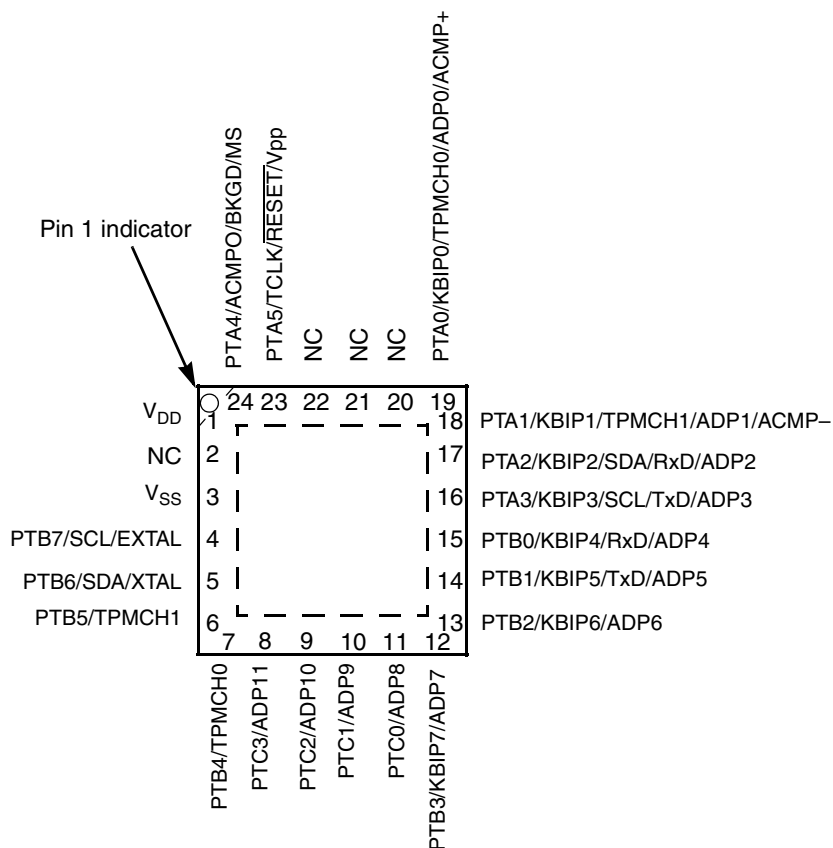


Figure 2. MC9RS08KB12 Series 24-Pin QFN Package

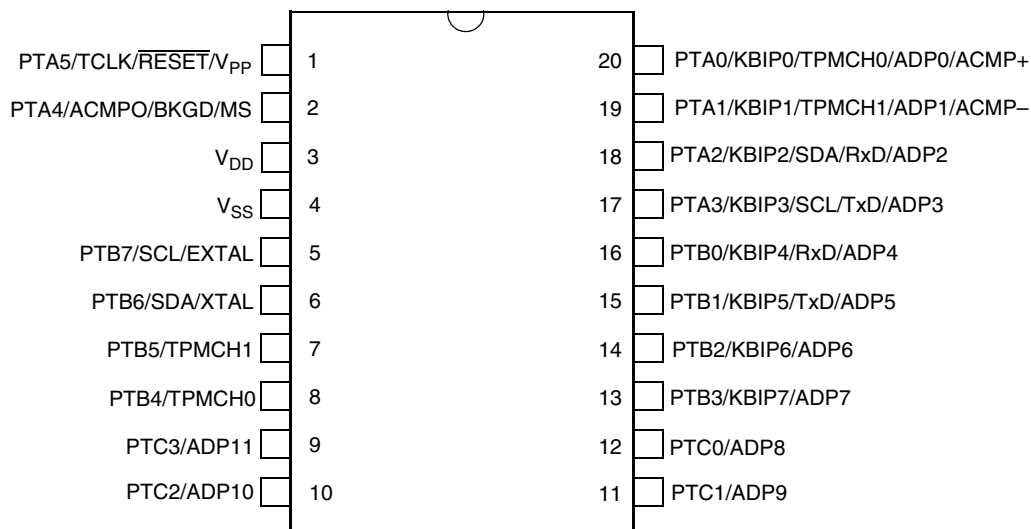


Figure 3. MC9RS08KB12 Series 20-Pin SOIC Package

Table 2. Parameter Classifications

D	Those parameters are derived mainly from simulations.
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NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

3.3 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 3 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this chapter.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, V_{SS} or V_{DD}) or the programmable pull-up resistor associated with the pin is enabled.

Table 3. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	−0.3 to 5.8	V
Maximum current into V_{DD}	I_{DD}	120	mA
Digital input voltage	V_{In}	−0.3 to $V_{DD} + 0.3$	V
Instantaneous maximum current Single pin limit (applies to all port pins) ^{1, 2, 3}	I_D	±25	mA
Storage temperature range	T_{stg}	−55 to 150	°C

¹ Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

² All functional non-supply pins are internally clamped to V_{SS} and V_{DD} except the \overline{RESET}/V_{PP} pin which is internally clamped to V_{SS} only.

³ Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD} , the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.

3.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits and it is user-determined rather than being controlled by the MCU design. In order to take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of

Electrical Characteristics

unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 4. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	T_L to T_H -40 to 85	°C
Maximum junction temperature	T_{JMAX}	150	°C
Thermal resistance 24-pin QFN	θ_{JA}	113	°C/W
Thermal resistance 20-pin SOIC	θ_{JA}	83	°C/W
Thermal resistance 16-pin SOIC NB	θ_{JA}	103	°C/W
Thermal resistance 16-pin TSSOP	θ_{JA}	29	°C/W
Thermal resistance 8-pin SOIC	θ_{JA}	150	°C/W
Thermal resistance 8-pin DFN	θ_{JA}	110	°C/W

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \quad \text{Eqn. 1}$$

where:

T_A = Ambient temperature, °C

θ_{JA} = Package thermal resistance, junction-to-ambient, °C /W

$P_D = P_{int} + P_{I/O}$

$P_{int} = I_{DD} \times V_{DD}$, Watts chip internal power

$P_{I/O}$ = Power dissipation on input and output pins user determined

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273^\circ\text{C}) \quad \text{Eqn. 2}$$

Solving [Equation 1](#) and [Equation 2](#) for K gives:

$$K = P_D \times (T_A + 273^\circ\text{C}) + \theta_{JA} \times (P_D)^2 \quad \text{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from [Equation 3](#) by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J can be obtained by solving [Equation 1](#) and [Equation 2](#) iteratively for any value of T_A .

3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions must be used to avoid exposure to static discharge.

Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

During the device qualification ESD stresses were performed for the human body model (HBM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 5. ESD and Latch-Up Test Conditions

Model	Description	Symbol	Value	Unit
Human body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	1	—
Latch-up	Minimum input voltage limit	—	-2.5	V
	Maximum input voltage limit	—	7.5	V

Table 6. ESD and Latch-Up Protection Characteristics

No.	Rating ¹	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	± 2000	—	V
2	Charge device model (CDM)	V_{CDM}	± 500	—	V
3	Latch-up current at $T_A = 85^\circ\text{C}$	I_{LAT}	± 100	—	mA

¹ Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

3.6 DC Characteristics

This section includes information about power supply requirements, I/O pin characteristics, and power supply current in various operating modes.

Table 7. DC Characteristics (Temperature Range = -40 to 85°C Ambient)

No.	C	Parameter	Symbol	Min	Typical	Max	Unit
1	—	Supply voltage (run, wait and stop modes.) $0 < f_{BUS} < 10\text{ MHz}$	V_{DD}	1.8	—	5.5	V
2	C	Minimum RAM retention supply voltage applied to V_{DD}	V_{RAM}	0.8 ¹	—	—	V
3	P	Low-voltage detection threshold (V_{DD} falling) (V_{DD} rising)	V_{LVD}	1.80 1.88	1.86 1.94	1.95 2.05	V
4	C	Power on RESET (POR) voltage	V_{POR}^1	0.9	—	1.7	V
5	C	Input high voltage ($V_{DD} > 2.3\text{V}$) (all digital inputs)	V_{IH}	$0.70 \times V_{DD}$	—	—	V
6	C	Input high voltage ($1.8\text{ V} \leq V_{DD} \leq 2.3\text{ V}$) (all digital inputs)	V_{IH}	$0.85 \times V_{DD}$	—	—	V
7	C	Input low voltage ($V_{DD} > 2.3\text{ V}$) (all digital inputs)	V_{IL}	—	—	$0.30 \times V_{DD}$	V
8	C	Input low voltage ($1.8\text{ V} \leq V_{DD} \leq 2.3\text{ V}$) (all digital inputs)	V_{IL}	—	—	$0.30 \times V_{DD}$	V
9	C	Input hysteresis (all digital inputs)	V_{hys}^1	$0.06 \times V_{DD}$	—	—	V
10	P	Input leakage current (per pin) $V_{IN} = V_{DD}$ or V_{SS} , all input only pins	I_{InI}	—	0.025	1.0	μA
11	P	High impedance (off-state) leakage current (per pin) $V_{IN} = V_{DD}$ or V_{SS} , all input/output	I_{IOZ}	—	0.025	1.0	μA
12	P	Internal pullup resistors ² (all port pins)	R_{PU}	20	45	65	$\text{k}\Omega$
13	P	Internal pulldown resistors ² (all port pins)	R_{PD}	20	45	65	$\text{k}\Omega$
14	C	Output high voltage — Low drive ($PTxDSn = 0$) 5 V, $I_{Load} = 2\text{ mA}$ 3 V, $I_{Load} = 1\text{ mA}$ 1.8 V, $I_{Load} = 0.5\text{ mA}$	V_{OH}	$V_{DD} - 0.8$	— — —	— — —	V
		Output high voltage — High drive ($PTxDSn = 1$) 5 V, $I_{Load} = 5\text{ mA}$ 3 V, $I_{Load} = 3\text{ mA}$ 1.8 V, $I_{Load} = 2\text{ mA}$		$V_{DD} - 0.8$	— — —	— — —	
15	C	Maximum total IOH for all port pins	$ I_{OHT} $	—	—	40	mA

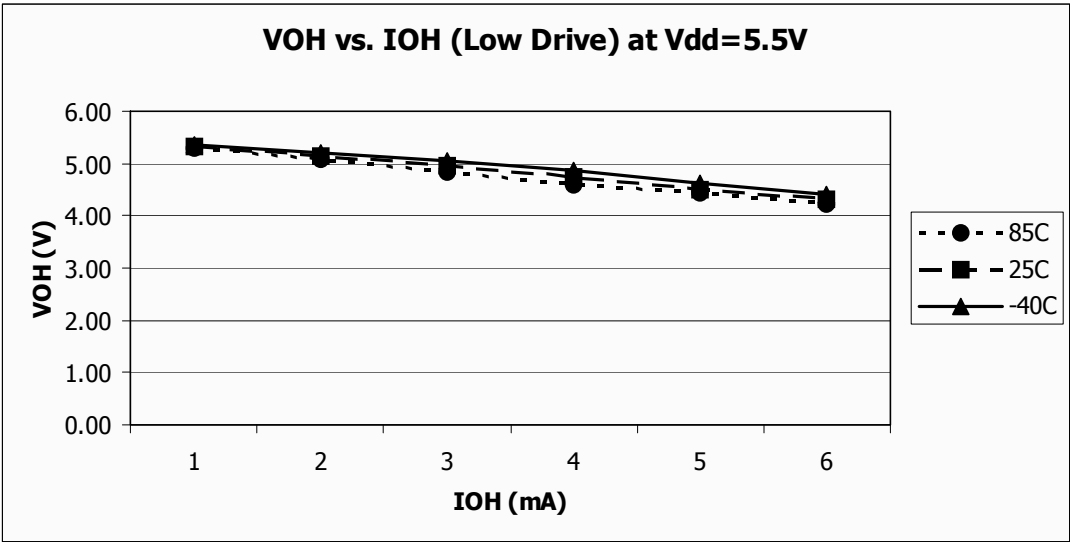


Figure 7. Typical V_{OH} vs. I_{OH}
 $V_{DD} = 5.5 \text{ V}$ (Low Drive)

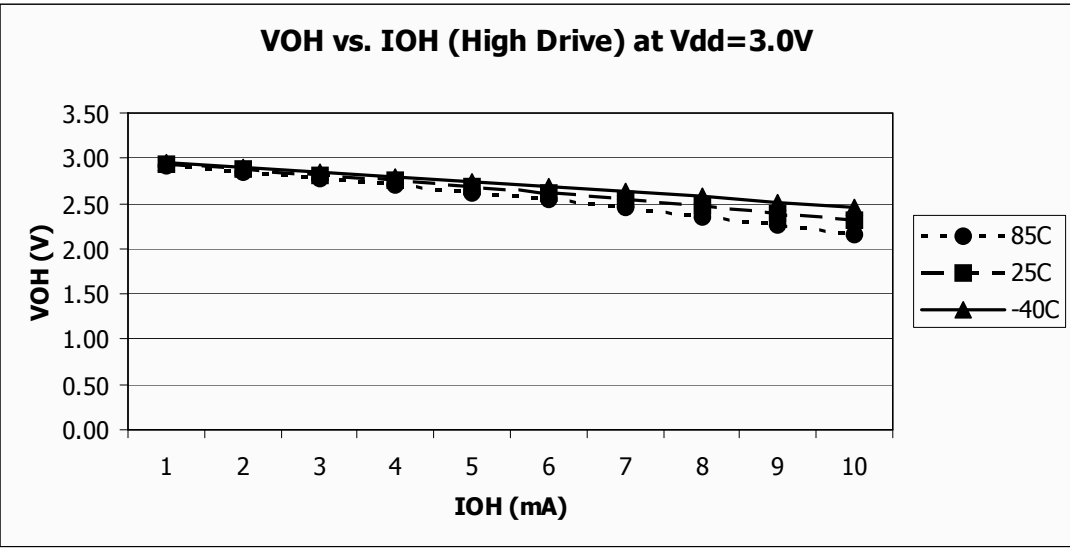


Figure 8. Typical V_{OH} vs. I_{OH}
 $V_{DD} = 3.0 \text{ V}$ (High Drive)

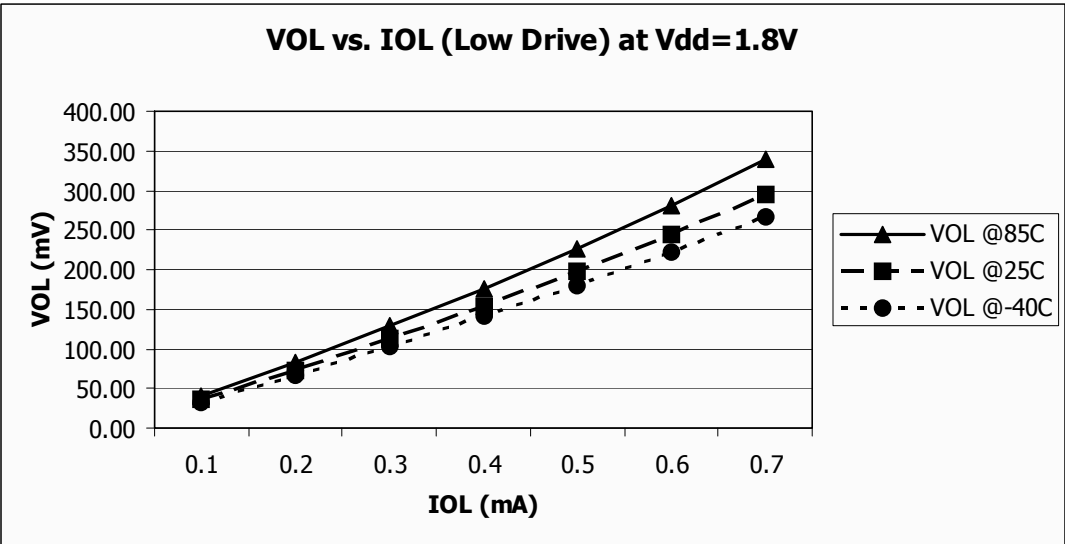


Figure 17. Typical V_{OL} vs. I_{OL}
 $V_{DD} = 1.8\text{ V}$ (Low Drive)

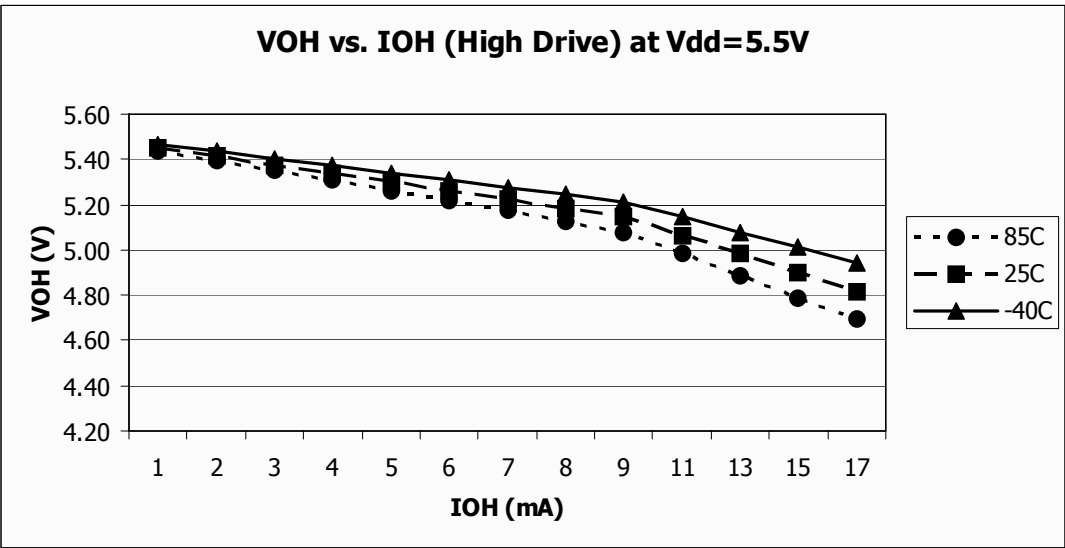


Figure 18. Typical I_{OH} vs. $V_{DD}-V_{OH}$
 $V_{DD} = 5.5\text{ V}$ (High Drive)

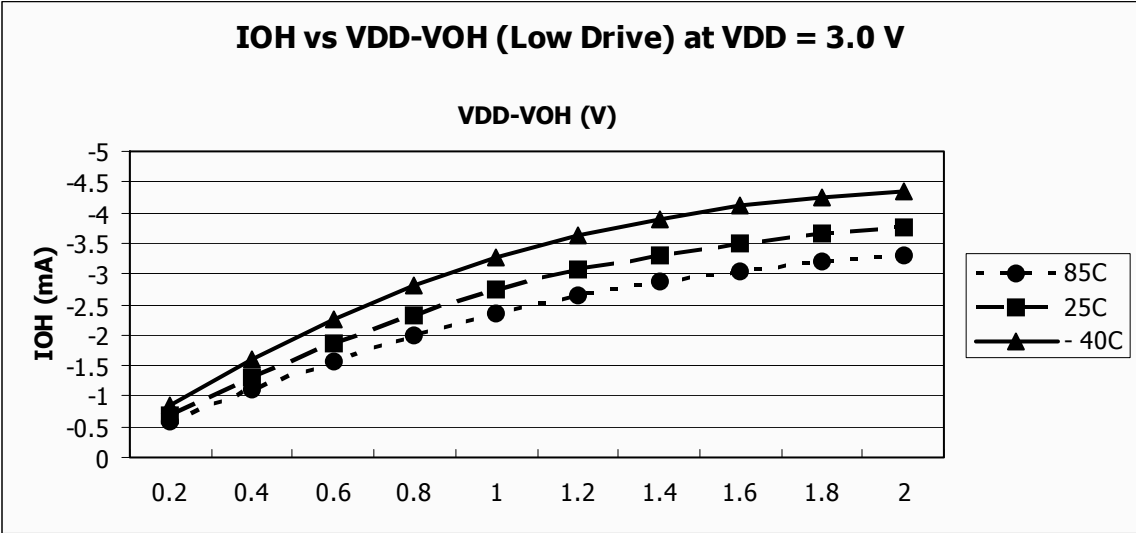


Figure 21. Typical I_{OH} vs. $V_{DD}-V_{OH}$
 $V_{DD} = 3\text{ V}$ (Low Drive)

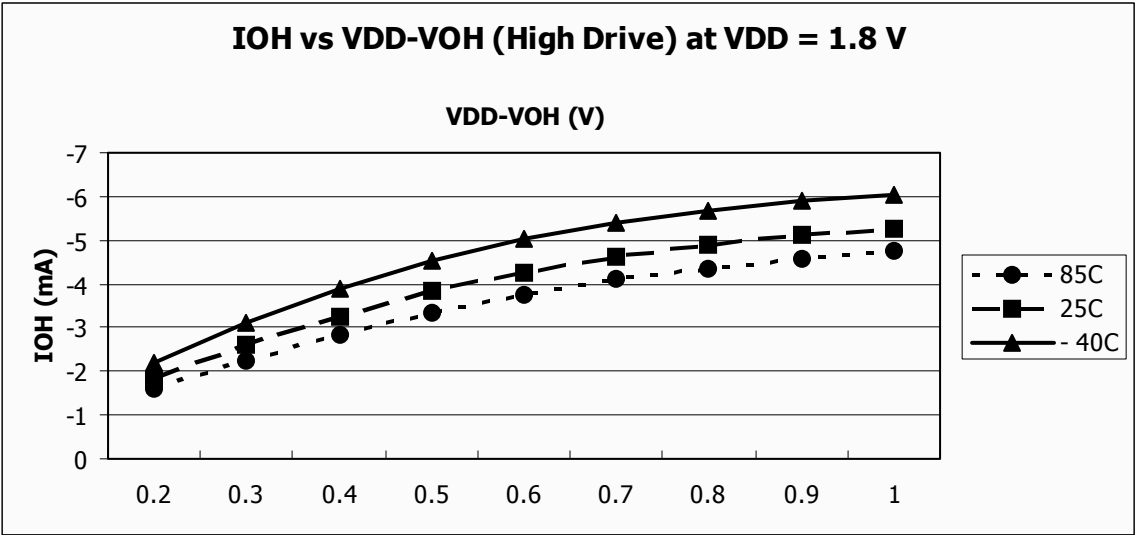


Figure 22. Typical I_{OH} vs. $V_{DD}-V_{OH}$
 $V_{DD} = 1.8\text{ V}$ (High Drive)

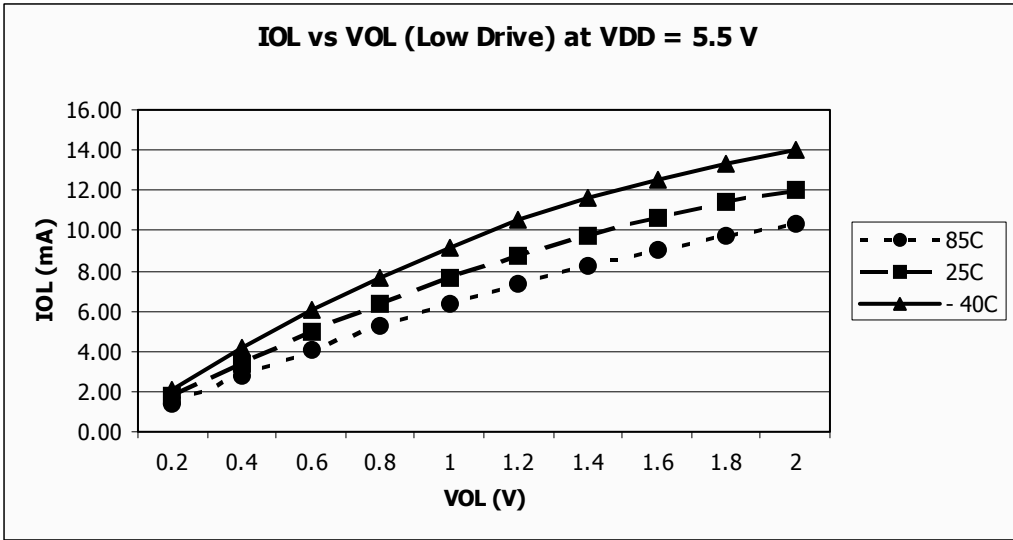


Figure 25. Typical I_{OL} vs. V_{OL}
 $V_{DD} = 5.5\text{ V}$ (Low Drive)

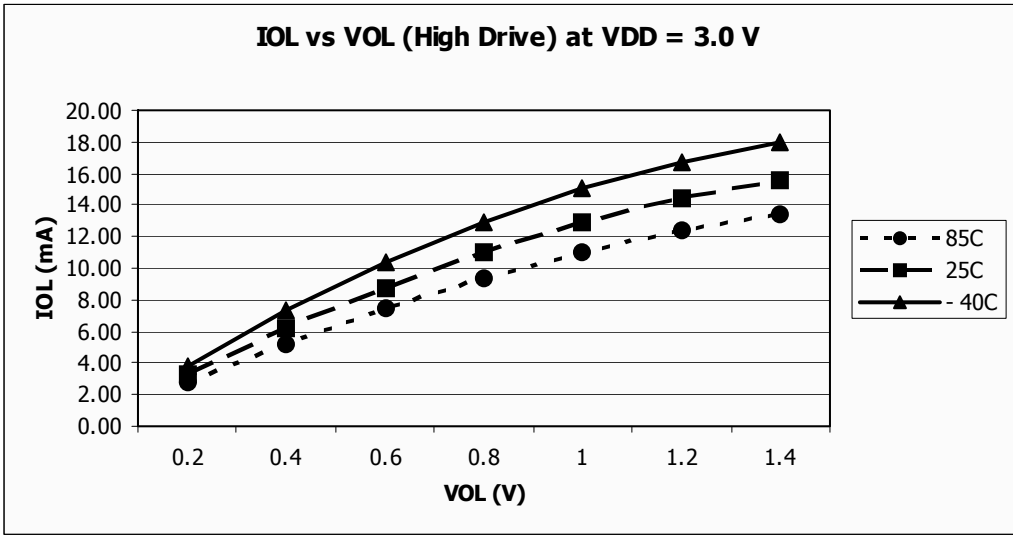


Figure 26. Typical I_{OL} vs. V_{OL}
 $V_{DD} = 3\text{ V}$ (High Drive)

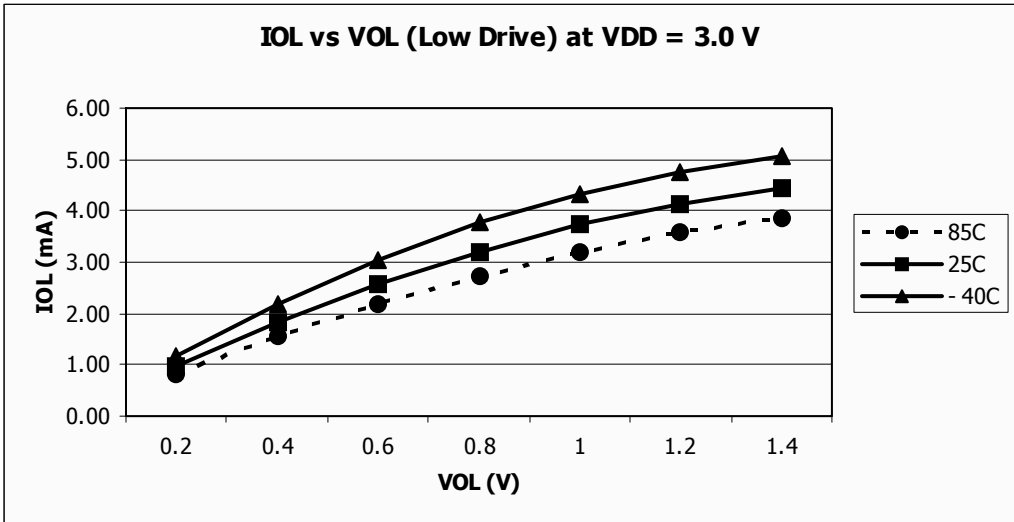


Figure 27. Typical I_{OL} vs. V_{OL}
 $V_{DD} = 3\text{ V}$ (Low Drive)

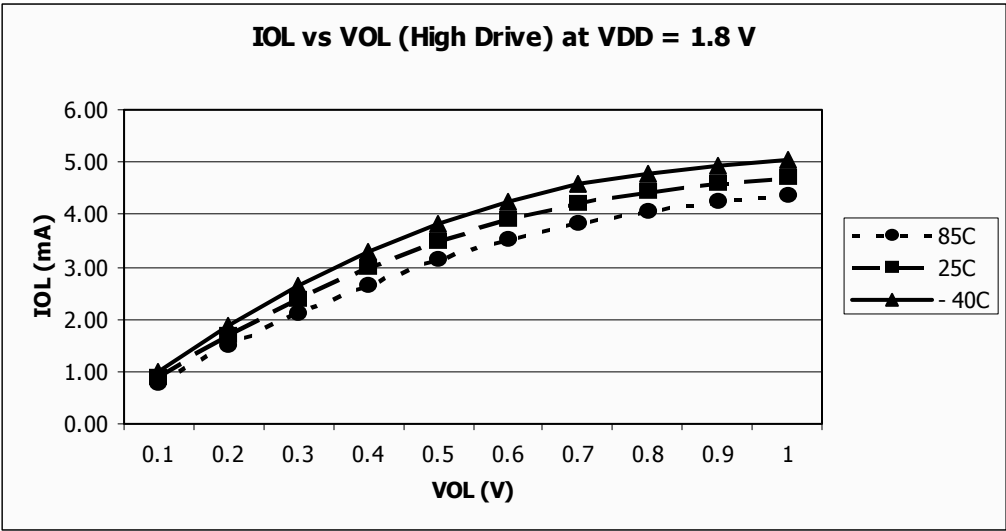


Figure 28. Typical I_{OL} vs. V_{OL}
 $V_{DD} = 1.8\text{ V}$ (High Drive)

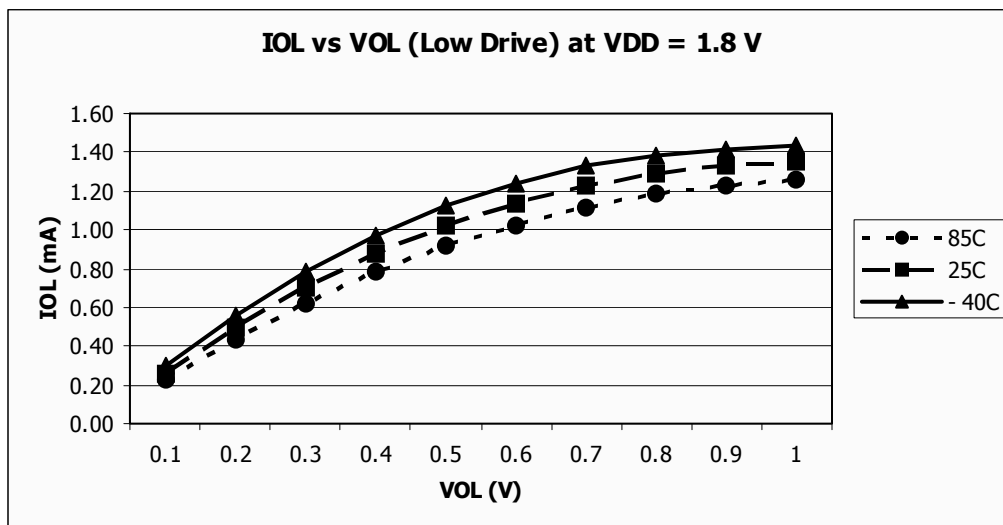


Figure 29. Typical I_{OL} vs. V_{OL}
 $V_{DD} = 1.8\text{ V}$ (Low Drive)

3.7 Supply Current Characteristics

Table 8. Supply Current Characteristics

N	C	Parameter	Symbol	V_{DD} (V)	Typical	Max ¹	Temp. (°C)	Unit
1	P	Run supply current ² measured at ($f_{Bus} = 10\text{ MHz}$)	R_{IDD10}	5	3.45 3.48 3.53	7	-40 25 85	mA
2	C			3	3.39 3.42 3.49	—	-40 25 85	
3	C			1.80	2.40 2.42 2.44	—	-40 25 85	
4	C	Run supply current ³ measured at ($f_{Bus} = 1.25\text{ MHz}$)	R_{IDD1}	5	0.93 0.96 0.99	—	-40 25 85	mA
5	T			3	0.91 0.92 0.92	—	-40 25 85	
6	T			1.80	0.66 0.67 0.68	—	-40 25 85	

Table 8. Supply Current Characteristics (continued)

N	C	Parameter	Symbol	V _{DD} (V)	Typical	Max ¹	Temp. (°C)	Unit
7	C	Wait mode supply current ³ measured at (f _{Bus} = 2.00 MHz)	W _I DD2	5	841.13 859.98 873.69	—	–40 25 85	μA
8	T			3	840.21 850.60 846.67	—	–40 25 85	
9	T			1.80	630.64 635.10 643.67	—	–40 25 85	
10	C	Wait mode supply current ³ measured at (f _{Bus} = 1.00 MHz)	W _I DD1	5	667.86 683.38 688.02	—	–40 25 85	μA
11	T			3	666.34 672.79 669.15	—	–40 25 85	
12	T			1.80	505.39 509.28 502.52	—	–40 25 85	
13	P	Stop mode supply current	S _I DD	5	1.15 1.40 7.67	11	–40 25 85	μA
14	C			3	1.05 1.26 4.52	—	–40 25 85	
15	C			1.80	0.39 0.56 4.21	—	–40 25 85	
16	C	ADC adder from stop ³	—	5	128.86 140.44 154.97	—	–40 25 85	μA
17	T			3	102.98 111.71 118.33	—	–40 25 85	
18	T			1.80	54.77 66.33 74.42	—	–40 25 85	
19	C	ACMP adder from stop (ACME = 1)	—	5	14.43 15.96 16.77	—	–40 25 85	μA
20	T			3	14.37 14.72 14.45	—	–40 25 85	
21	T			1.80	13.05 14.02 12.92	—	–40 25 85	

Table 8. Supply Current Characteristics (continued)

N	C	Parameter	Symbol	V _{DD} (V)	Typical	Max ¹	Temp. (°C)	Unit
22	C	RTI adder from stop with 1 kHz clock source enabled ⁴	—	5	0.10 0.10 0.17	—	–40 25 85	μA
23	T			3	0.02 0.06 0.02	—	–40 25 85	
24	T			1.80	0.40 0.45 0.20	—	–40 25 85	
25	T	RTI adder from stop with 32.768KHz external clock source reference enabled	—	5	0.70 1.08 1.94	—	–40 25 85	μA
26	T			3	0.56 0.56 0.62	—	–40 25 85	
27	T			1.80	0.70 0.86 0.50	—	–40 25 85	
28	C	LVI adder from stop (LVDE = 1 and LVDSE = 1)	—	5	58.93 68.27 76.60	—	–40 25 85	μA
29	T			3	58.89 61.98 63.45	—	–40 25 85	
30	T			1.80	52.84 54.52 52.49	—	–40 25 85	

¹ Maximum value is measured at the nominal V_{DD} voltage times 10% tolerance. Values given here are preliminary estimates prior to completing characterization.

² Not include any DC loads on port pins.

³ Required asynchronous ADC clock and LVD to be enabled.

⁴ Most customers are expected to find that auto-wakeup from stop can be used instead of the higher current wait mode. Wait mode typical is 672.79 μA at 3 V and 509.28 μA at 1.8 V with f_{BUS} = 1 MHz.

3.8 External Oscillator (XOSC) Characteristics

Table 9. Oscillator Electrical Specifications (Temperature Range = -40 to 85°C Ambient)

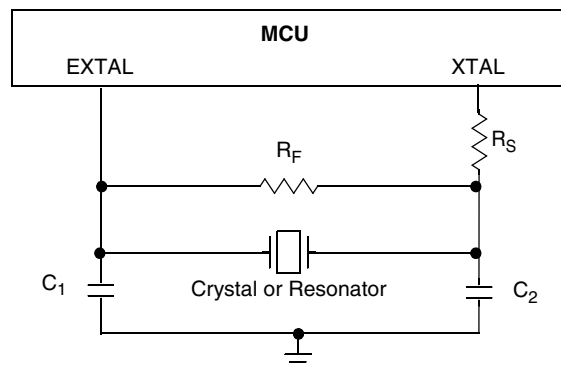
Num	C	Rating	Symbol	Min	Typical ¹	Max	Unit
1	C	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1)					
		Low range (RANGE = 0)	f_{lo}	32	—	38.4	kHz
		High range (RANGE = 1) FEE or FBE mode ²	f_{hi}	1	—	5	MHz
		High range (RANGE = 1, HGO = 1) FBELP mode	f_{hi-hgo}	1	—	16	MHz
		High range (RANGE = 1, HGO = 0) FBELP mode	f_{hi-lp}	1	—	8	MHz
2	D	Load capacitors	C_1, C_2	See crystal or resonator manufacturer's recommendation.			
3	D	Feedback resistor	R_F	—	10	—	M Ω
		Low range (32 kHz to 100 kHz) High range (1 MHz to 16 MHz)		—	1	—	
4	D	Series resistor	R_S	—	0	—	k Ω
		Low range, low gain (RANGE = 0, HGO = 0)		—	100	—	
		Low range, high gain (RANGE = 0, HGO = 1)		—	0	—	
		High range, low gain (RANGE = 1, HGO = 0)		—	0	—	
		High range, high gain (RANGE = 1, HGO = 1)		—	0	0	
		≥ 8 MHz 4 MHz 1 MHz		—	0	10 20	
5	C	Crystal start-up time ³					
		Low range, low gain (RANGE = 0, HGO = 0)	$t_{CSTL-LP}$	—	200	—	ms
		Low range, high gain (RANGE = 0, HGO = 1)	$t_{CSTL-HGO}$	—	400	—	
		High range, low gain (RANGE = 1, HGO = 0) ⁴	$t_{CSTH-LP}$	—	5	—	
		High range, high gain (RANGE = 1, HGO = 1) ⁴	$t_{CSTH-HGO}$	—	20	—	
6	D	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1)	f_{extal}	0.03125	—	5	MHz
		FEE or FBE mode ²		0	—	40	
		FBELP mode					

¹ Typical data was characterized at 5.0 V, 25 °C or is recommended value.

² The input clock source must be divided using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

³ This parameter is characterized and not tested on each device. Proper PC board layout procedures must be followed to achieve specifications.

⁴ 4 MHz crystal.



3.9 AC Characteristics

This section describes AC timing characteristics for each peripheral system.

Table 14. 10-Bit ADC Operating Conditions (continued)

Characteristic	Conditions	Symb	Min	Typ ¹	Max	Unit	Comment
ADC conversion clock Freq.	High speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	
	Low power (ADLPC=1)		0.4	—	4.0		

¹ Typical values assume $V_{DDAD} = 5.0$ V, Temp = 25 °C, $f_{ADCK} = 1.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

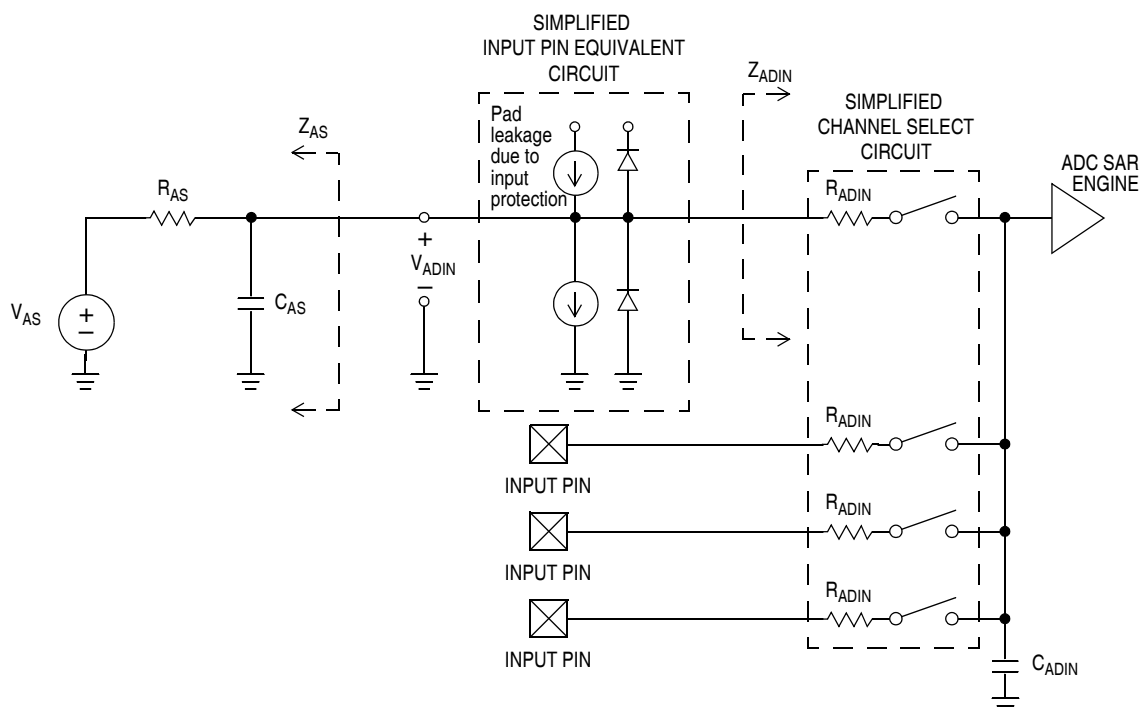


Figure 34. ADC Input Impedance Equivalency Diagram

Table 15. 10-Bit ADC Characteristics ($V_{REFH} = V_{DDAD}$, $V_{REFL} = V_{SSAD}$, 2.7 V < $V_{DDAD} < 5.5$ V)

C	Characteristic	Conditions	Symb	Min	Typ ¹	Max	Unit	Comment
T	Supply Current ADLPC = 1 ADLSMP = 1 ADCO = 1		I_{DDAD}	—	133	—	μA	
T	Supply Current ADLPC = 1 ADLSMP = 0 ADCO = 1		I_{DDAD}	—	218	—	μA	
T	Supply Current ADLPC = 0 ADLSMP = 1 ADCO = 1		I_{DDAD}	—	327	—	μA	

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